

## EAST Search History

## EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	1	((substrate wafer) near (cutting near different)) same (resistivity resistivities) same temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:28
L3	27	((substrate wafer) near (cutting )) same (resistivity resistivities) same temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:30
L15	2036	438/507,566-569,74,77,81,93-94. ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:33
L19	5	(( (cutting near (plane\$1 position\$1))) same (resistivity resistivities) same temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:35
L20	5	(( (cutting dicing segment\$3dividing) near (plane\$1 position\$1))) same (resistivity resistivities) same temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:36
L21	0	20 not 19	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:36
L22	5355	(( (plane\$1 position\$1))) same (resistivity resistivities) same temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:36
L23	4709	257/443,448,459,461,466.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:36

L24	6633	15 or 23	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:36
L25	4709	23 and 24	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:36
L26	41	22 and 24	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:37
L27	1	("2002/0168856").URPN.	USPAT	OR	ON	2010/09/17 10:38
L28	101	(( cutting )) same (depend depending) same (resistivity resistivities) same temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:40
L29	135715	vapor near phase	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:40
L30	2	28 and 29	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:40
L32	19	("3651386"   "4454495"   "4919542"   "4996077"   "5154514"   "5245309"   "5297438"   "5415699"   "5429070"   "5435646"   "5493266"   "5502355"   "5564830"   "5614055"   "5831277"   "5900071"   "5907161"   "5947601").PN. OR ("6257760"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/17 10:47
L33	12	("20010053600"   "5326170"   "5331676"   "5593923"   "5780360"   "6132081"   "6136613"   "6136699"   "6257760"   "6329670"   "6399487"). PN. OR ("6517235").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/17 10:48
L35	2	("2003/0077870").URPN.	USPAT	OR	ON	2010/09/17 11:41
L36	0	(Fe near InP) with (cutting) with (temperature resistivity) with (heating) with (epitaxy epitaxially epitaxial)	USPAT	OR	ON	2010/09/17 11:43

L37	0	(Fe near InP) with (cutting) with (temperature resistivity) with (heating) with (epitaxy epitaxially epitaxial)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:43
L38	0	(Fe near semiconductor) with (cutting) with (temperature resistivity) with (heating) with (epitaxy epitaxially epitaxial)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:43
L39	0	(single near crystal) with (cutting) with (temperature resistivity) with (heating) with (epitaxy epitaxially epitaxial)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:44
L40	2	(substrate) with (cutting) with (temperature resistivity) with (heating) with (epitaxy epitaxially epitaxial)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:44
L41	35622	(epitaxy epitaxially epitaxial) with (vapor phase near reproducible)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:48
L42	0	(epitaxy epitaxially epitaxial) with (vapor near phase near reproducible)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:48
L43	16626	(epitaxy epitaxially epitaxial) with (vapor near phase )	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:48
L44	3205	(single near crystal) with cutting	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:48
L45	85	((single near crystal) with cutting) with (heating)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:49

L46	0	43 and 45	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:49
L47	6974	(substrate wafer) with ( epitaxy epitaxially epitaxial) with (vapor near phase ))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:49
L48	104	44 and 47	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:49
L49	6752	(substrate wafer) with ( epitaxy epitaxial) with (vapor near phase ))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:52
L50	100	44 and 49	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:52
L51	1	"10589733"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:55
L52	0	(vapor near phase near reproducible)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 12:02
L53	0	(vapor near phase near reproduc\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 12:02
L54	5093	(vapor near phase near produc\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 12:02

L55	0	(vapor near phase near (re near produc\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 12:03
L56	5829	(substrates) with (epitaxial epitaxy) with (vapor near phase )	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 12:03
L57	96	44 and 56	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 12:03
L58	457	(Fe near InP)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 12:04
L59	1	57 and 58	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 12:04

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